

**AMENDMENTS TO THE ABSTRACT**

Please amend the Abstract to read as follows. A clean copy of the Abstract follows on the next page.

**ABSTRACT**

Using a lower electrode as a photomask, a lyophobic region having generally the same pattern as that of the lower electrode and a yophobic-lyophilic region having a pattern which is generally the inversion of the lower electrode pattern are formed on an insulating film. A conductive ink is applied to the yophobic lyophobic region and baked. Thus, an upper electrode having a pattern which is generally the inversion of the lower electrode pattern is formed in a self-alignment manner. Therefore no misalignment occurs even if a printing method is used. Thus, a semiconductor device such as an active-matrix thin-film transistor substrate can be fabricated by using a printing method.

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Using a lower electrode as a photomask, a lyophobic region having generally the same pattern as that of the lower electrode and a lyophilic region having a pattern which is generally the inversion of the lower electrode pattern are formed on an insulating film. A conductive ink is applied to the lyophobic region and baked. Thus, an upper electrode having a pattern which is generally the inversion of the lower electrode pattern is formed in a self-alignment manner. Therefore no misalignment occurs even if a printing method is used. Thus, a semiconductor device such as an active-matrix thin-film transistor substrate can be fabricated by using a printing method.